depositing at least one of the thin film device layers by a separation in a separable layer on which the at least one thin film device layer is formed.

3. (Three Times Amended) The method of forming a three-dimensional device according to claim 1, further comprising forming the at least one thin film device layer on a second substrate with the separable layer therebetween; and

irradiating the separable layer with light to cause a separation in at least one of the separable layer and at an interface so that the at least one thin film device layer on the second substrate is transferred to the first substrate of the three-dimensional device.

4. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

5. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.

6. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the light being a laser beam.

7. (Twice Amended) The method of forming a three-dimensional device according to claim 3, the separable layer comprising one of amorphous silicon, ceramic, metal, and organic polymeric material.

8. (Twice Amended) The method of forming a three-dimensional device according to claim 1, each thin film device layer comprising electrodes electrically connecting two adjacent thin film device layers to each other.

9. (Twice Amended) The method of forming a three-dimensional device according to claim 8, the connecting electrodes being provided on both surfaces of each thin film device layer.

10. (Twice Amended) The method of forming a three-dimensional device according to claim 8, the three dimensional device further comprising an anisotropic conductive film, the method further comprising joining two adjacent thin film device layers to each other with the anisotropic conductive film therebetween.

11. (Twice Amended) The method of forming a three-dimensional device according to claim 1, in two selected layers of the thin film device layers, a first layer has a light-emitting section and a second layer has a light-receiving section, the light-emitting section and the light-receiving section enabling optical communication between the two layers.

12. (Twice Amended) The method of forming a three-dimensional device according to claim 1, the at least one thin film device layer deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

13. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a plurality of thin film transistors.

14. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array.

15. (Twice Amended) The method of forming a three-dimensional device according to claim 1, a plurality of layers among the thin film device layers comprising one memory.

16. (Twice Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array, and at least one other thin film device layers comprises a logic circuit.

17. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit driving the memory cell array.

18. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design rules.

19. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design parameters.

20. (Twice Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed by different fabricating processes.

21. (Amended) A method for manufacturing a three-dimensional device having a plurality of thin film device layers on a first substrate, comprising:

forming at least one thin film device layer on a second substrate with a separable layer therebetween; and

irradiating the separable layer with light to cause a separation in at least one of the separable layers and at an interface so that the at least one thin film device layer is transferred to the first substrate.

22. (Amended) The method for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

23. (Amended) The method for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.

24. (Amended) The method for manufacturing a three-dimensional device according to claim 21, the light being a laser beam.